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FDS6875

Dual P-Channel 2.5V Specified PowerTrench™ MOSFET

General Description

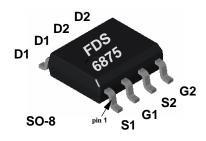
These P-Channel 2.5V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

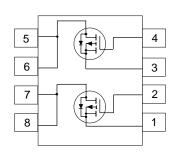
These devices are well suited for portable electronics applications: load switching and power management, battery charging and protection circuits.

Features

- Low gate charge (23nC typical).
- High performance trench technology for extremely low R_{DS/OND}.
- High power and current handling capability.







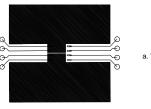
Absolute Maximum Ratings $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	FDS6875	Units
V _{DSS}	Drain-Source Voltage	-20	V
V _{GSS}	Gate-Source Voltage	±8	V
D	Drain Current - Continuous (Note 1a)	-6	А
	- Pulsed	-20	
P _D	Power Dissipation for Dual Operation	2	W
	Power Dissipation for Single Operation (Note 1a)	1.6	
	(Note 1b)	1	
	(Note 1c)	0.9	
T _J ,T _{STG}	Operating and Storage Temperature Range	-55 to 150	°C
THERMA	L CHARACTERISTICS		
R _{eJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	°C/W
R _{eJC}	Thermal Resistance, Junction-to-Case (Note 1)	40	°C/W

Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHAR	ACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		-20			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	I _D = -250 μA, Referenced	to 25 °C		-21		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, \ V_{GS} = 0 \text{ V}$				-1	μA
			$T_J = 55^{\circ}C$			-10	μΑ
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHARA	CTERISTICS (Note 2)			ı	I	I	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-0.4	-0.8	-1.5	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp. Coefficient	I _D = 250 µA, Referenced to 25 °C			2.8		mV/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_{D} = -6 \text{ A}$			0.024	0.03	Ω
, ,			T _J =125°C		0.033	0.048	
		$V_{GS} = -2.5 \text{ V}, I_D = -5.3 \text{ A}$			0.032	0.04	
I _{D(ON)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \ V_{DS} = -5 \text{ V}$		-20			Α
g _{FS}	Forward Transconductance	$V_{DS} = -4.5 \text{ V}, I_{D} = -6 \text{ A}$			22		S
DYNAMIC (CHARACTERISTICS	•		•	•		
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$			2250		pF
C _{oss}	Output Capacitance				500		pF
C _{rss}	Reverse Transfer Capacitance				200		pF
SWITCHING	CHARACTERISTICS (Note 2)						
t _{D(on)}	Turn - On Delay Time	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ A}$			8	16	ns
t,	Turn - On Rise Time	V_{GEN} = -4.5 V, R_{GEN} = 6 Ω			15	27	ns
t _{D(off)}	Turn - Off Delay Time				98	135	ns
t,	Turn - Off Fall Time				35	55	ns
Q_g	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -6 \text{ A},$			23	31	nC
Q_{gs}	Gate-Source Charge	V _{GS} = -5 V			3.9		nC
Q_{gd}	Gate-Drain Charge				5.5		nC
DRAIN-SOU	RCE DIODE CHARACTERISTICS AND MAX	(IMUM RATINGS					
I _s	Maximum Continuous Drain-Source Diode Forward Current					-1.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -1.3 A (Note 2)			-0.7	-1.2	V

Notes:

^{1.} $R_{g,u}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{g,c}$ is guaranteed by design while R_{gCA} is determined by the user's board design.



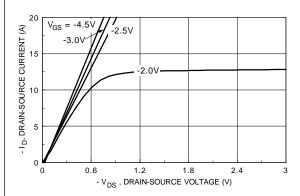




Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

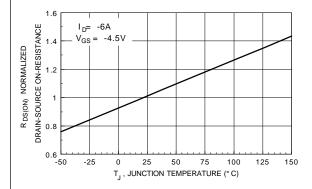
Typical Electrical Characteristics



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Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Dain Current and Gate Voltage.



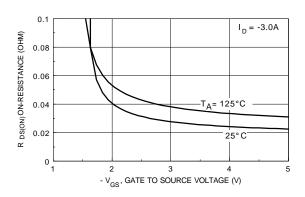
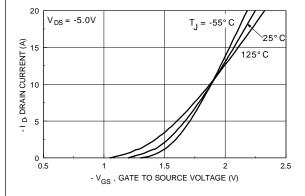


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



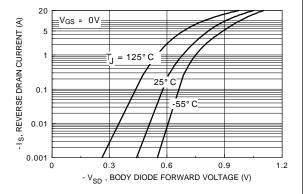
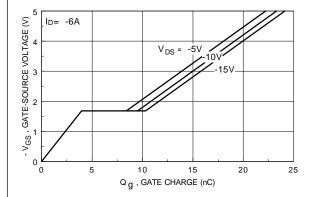


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics (continued)



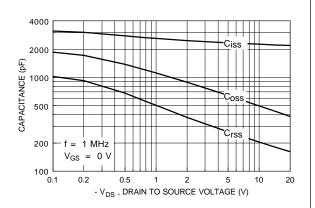
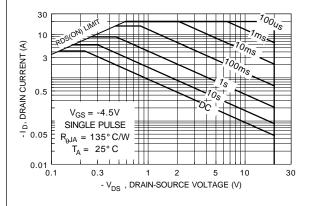


Figure 7. Gate Charge Characteristics.





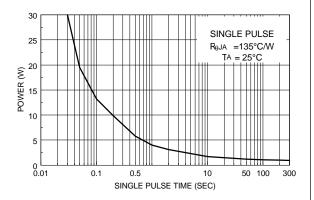


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

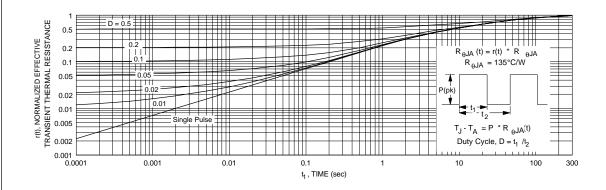


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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 E^2CMOS^{TM} PowerTrenchTM

FACT™ QFET™ FACT Quiet Series™ QS™

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